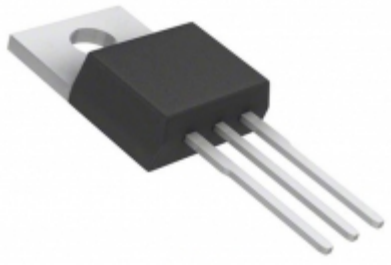

	<h2 style="color: red;">FDP030N06</h2> <p><b>Hersteller-Teilenummer:</b> FDP030N06</p> <p><b>Hersteller / Marke:</b> Fairchild/ON Semiconductor</p> <p><b>Teil der Beschreibung:</b> MOSFET N-CH 60V 120A TO220</p> <p><b>Datenblätter:</b> <a href="#">1.FDP030N06.pdf</a> <a href="#">2.FDP030N06.pdf</a></p> <p><b>RoHs Status:</b> Bleifrei / RoHS-konform</p> <p><b>Lagerzustand:</b> New original, 34023 pcs Stock Available.</p> <p><b>Liefern von:</b> Hong Kong</p> <p><b>Versandweg:</b> DHL/Fedex/TNT/UPS/EMS</p>
 <p style="font-size: small;">YIC International Co., Limited.</p>	
<p>Image may be representation. See specs for product details.</p>	

### Spezifikationen

Teilenummer	FDP030N06
Hersteller	Fairchild/ON Semiconductor
Beschreibung	MOSFET N-CH 60V 120A TO220
Kategorie	<a href="#">Diskrete Halbleiterprodukte &gt; Transistoren-FETs,</a>
Teilstatus	34023 pcs Stock
Serie	PowerTrench®
Technologie	MOSFET (Metal Oxide)
Betriebstemperatur	-55°C ~ 175°C (TJ)
Befestigungsart	Through Hole
Verpackung / Gehäuse	TO-220-3
Supplier Device-Gehäuse	TO-220AB
Verlustleistung (max)	231W (Tc)
Typ FET	N-Channel
FET-Merkmal	-
Drain-Source-Spannung (Vdss)	60V
Strom - Ununterbrochener Abfluss (Id) bei 25 ° C	120A (Tc)
Rds On (Max) @ Id, Vgs	3.2 mOhm @ 75A, 10V
VGS (th) (Max) @ Id	4.5V @ 250µA
Gate Charge (Qg) (Max) @ Vgs	151nC @ 10V
Eingabekapazität (Ciss) (Max) @ Vds	9815pF @ 25V
Antriebsspannung (Max Rds On, Min Rds On)	10V
Vgs (Max)	±20V
Verpackung	Tube

FDP030N06 ist neu im Original, Suche FDP030N06 Datenblätter, PDF, Inventar bei Y-IC.com Online, Bestellen Sie FDP030N06 Fairchild/ON Semiconductor mit Garantie und Vertrauen. Anfrage FDP030N06: Info@Y-IC.com

Sie können auch interessiert sein:

 Not Actual Photo YIC International Co., Limited.	 <p><b>FDP030N06B_F102</b> Fairchild/ON Semiconductor FDP030N06B_F102 Fairchild/ON Semiconductor</p>	 <p><b>FDP027N08B-F102</b> AMI Semiconductor / ON Semiconductor MOSFET N-CH 80V 120A TO-220-3</p>	 <p><b>FDP027N08B_F102</b> Fairchild/ON Semiconductor MOSFET N-CH 80V 120A TO-220-3</p>
 <p><b>FDP027N08B</b> AMI Semiconductor / ON Semiconductor MOSFET N-CH 80V 223A TO-220-3</p>	 <p><b>FDP030N06BTU</b> Fairchild/ON Semiconductor FDP030N06BTU FAIRCHILD</p>	 <p><b>FDP030N06B-F102</b> AMI Semiconductor / ON Semiconductor MOSFET N-CH 60V 120A TO-220-3</p>	 <p><b>FDP030N06</b> AMI Semiconductor / ON Semiconductor MOSFET N-CH 60V 120A TO220</p>

### heiße Teile

Mehr

<a href="#">FDP020N06B</a>	<a href="#">FDP023N08B</a>	<a href="#">FDP025N06</a>	<a href="#">FDP025N06</a>	<a href="#">FDP027N08B</a>
<a href="#">FDP027N08B</a>	<a href="#">FDP030N06</a>	<a href="#">FDP030N06B_F102</a>	<a href="#">FDP032N08</a>	<a href="#">FDP032N08</a>
<a href="#">FDP032N08B</a>	<a href="#">FDP036N10A</a>	<a href="#">FDP036N10A</a>	<a href="#">FDP038AN06A0</a>	<a href="#">FDP038AN06A0</a>
<a href="#">FDP038AN06AO</a>	<a href="#">FDP039N08B</a>	<a href="#">FDP040N06</a>	<a href="#">FDP040N06</a>	<a href="#">FDP045N10A</a>
<a href="#">FDP045N10A</a>	<a href="#">FDP047AN08</a>	<a href="#">FDP047AN08A0</a>	<a href="#">FDP047AN08A0</a>	<a href="#">FDP047AN08A0</a>
<a href="#">FDP047N08</a>	<a href="#">FDP047N08</a>	<a href="#">FDP047N08AO</a>	<a href="#">FDP047N10</a>	<a href="#">FDP047N10</a>
<a href="#">FDP050AN06A0</a>	<a href="#">FDP050AN06A0</a>	<a href="#">FDP050AN06A0</a>	<a href="#">FDP053N08B</a>	<a href="#">FDP053N08B_F102</a>
<a href="#">FDP054N10</a>	<a href="#">FDP054N10</a>	<a href="#">FDP060AN08A0</a>	<a href="#">FDP060AN08A0</a>	<a href="#">FDP060AN08A0</a>
<a href="#">FDP060N08A0</a>	<a href="#">FDP060N08AO</a>	<a href="#">FDP068AN08A0</a>	<a href="#">FDP070AN06A0</a>	<a href="#">FDP070AN06A0</a>
<a href="#">FDP070AN06A0</a>	<a href="#">FDP075N15A</a>	<a href="#">FDP075N15A</a>	<a href="#">FDP083N15A</a>	<a href="#">FDP083N15A</a>

Contact us: [Info@Y-IC.com](mailto:Info@Y-IC.com)

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